

PHP27NQ11T

N-channel TrenchMOS standard level FET Rev. 02 — 4 March 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance

1.3 Applications

DC-to-DC convertors

Switched-mode power supplies

1.4 Quick reference data

Table 1. **Quick reference**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	110	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> and <u>3</u>	-	-	27.6	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	107	W
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 27 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 11	-	12	-	nC
Static ch	naracteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 14 A; T_j = 25 °C; see <u>Figure 9</u> and <u>10</u>	-	40	50	mΩ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		$G \stackrel{\downarrow}{\mapsto} \overline{A}$
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHP27NQ11T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

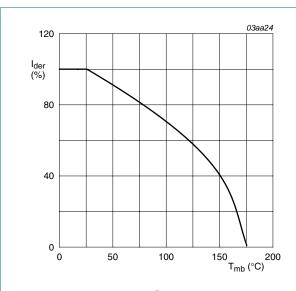
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	110	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	110	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{and } 3}$	-	27.6	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	20	Α
I_{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	112	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	107	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dr	ain diode				
Is	source current	T _{mb} = 25 °C	-	28	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	112	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 30 A; V_{sup} ≤ 100 V; unclamped; t_p = 0.05 ms; R_{GS} = 50 Ω	-	90	mJ

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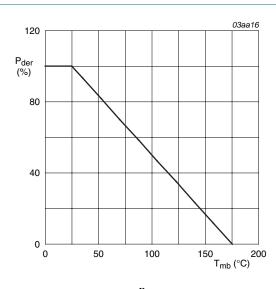
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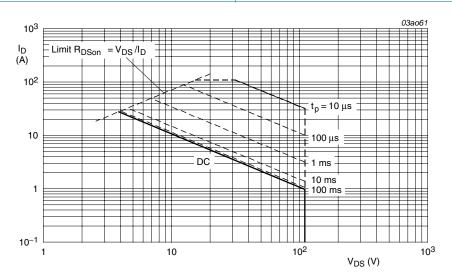
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse; $V_{GS} = 10V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

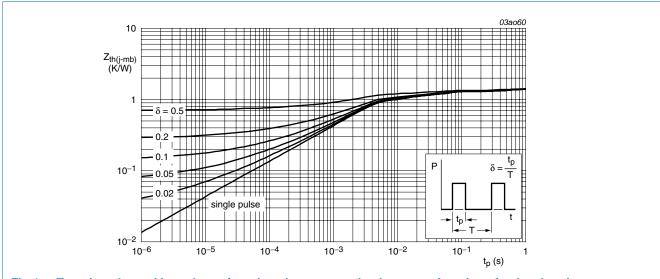


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	99	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	110	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 7 and 8	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 7 and 8	2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; see <u>Figure 7</u> and <u>8</u>	-	-	4.4	V
I _{DSS} drain leakage current	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS} gate leakage current	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R _{DSon} drain-source resistance	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 14 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 9 and 10	-	-	135	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 14 \text{ A}; T_j = 25 \text{ °C};$ see Figure 9 and 10	-	40	50	mΩ
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 27 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	30	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 11</u>	-	6	-	nC
Q_{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1240	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 12</u>	-	170	-	pF
C _{rss}	reverse transfer capacitance		-	100	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 10 \text{ V};$	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 °C$	-	43	-	ns
t _{d(off)}	turn-off delay time		-	32	-	ns
t _f	fall time		-	24	-	ns
Source-dr	rain diode					
V_{SD}	source-drain voltage	$I_S = 14 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	0.9	1.5	V
t _{rr}	reverse recovery time	$I_S = 14 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	60	-	ns
Qr	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	160	-	nC

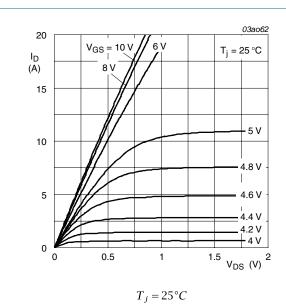
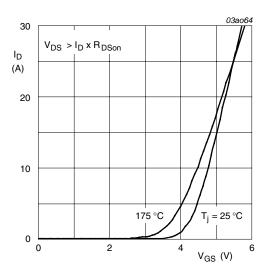


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_j = 25$ °C and 175°C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

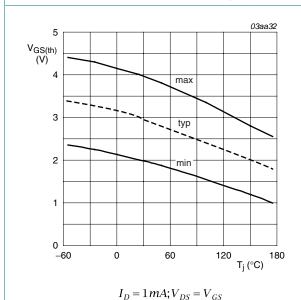
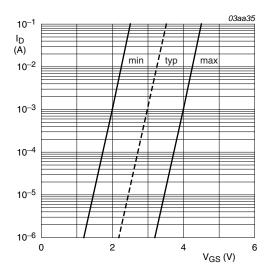


Fig 7. Gate-source threshold voltage as a function of junction temperature



 $T_{j}=25~^{\circ}C; V_{DS}=5V$ Fig 8. Sub-threshold drain current as a function of

gate-source voltage

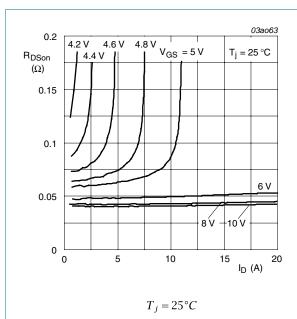


Fig 9. Drain-source on-state resistance as a function of drain current; typical values

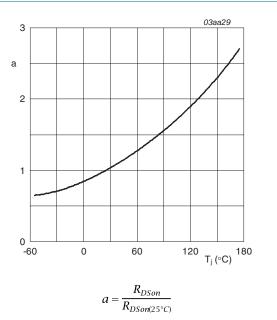


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

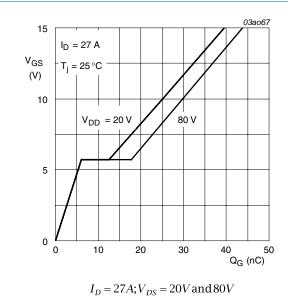


Fig 11. Gate-source voltage as a function of gate charge; typical values

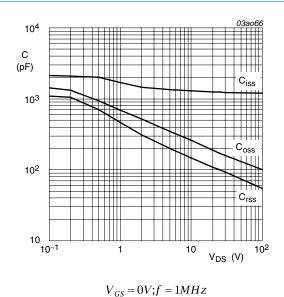
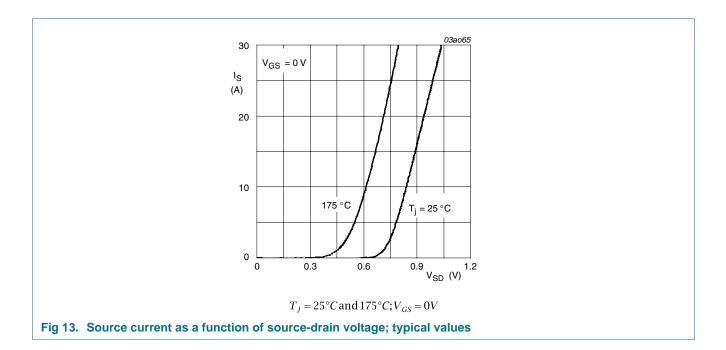
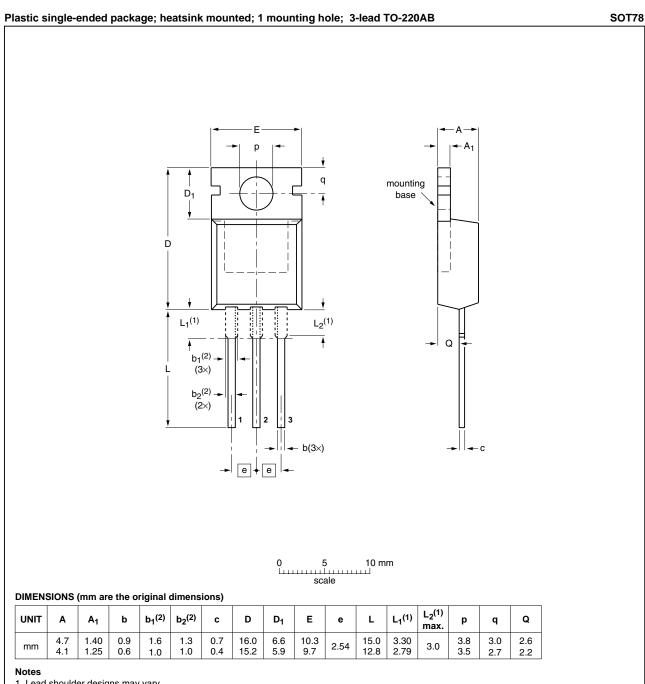


Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE D	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 14. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP27NQ11T_2	20100304	Product data sheet	-	PHP27NQ11T-01
Modifications:		of this data sheet has beer of NXP Semiconductors.	n redesigned to comply w	ith the new identity
	 Legal texts 	have been adapted to the	new company name whe	re appropriate.
PHP27NQ11T-01 (9397 750 13183)	20040517	Product data	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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